

forming at least one semiconductor layer on said porous layer;

separating said semiconductor layer from said substrate by forming a mechanical rupture within said porous layer.

C 103. The method for separating a semiconductor layer from a substrate according to <sup>Claim</sup> 97 or 102 wherein the method further comprises slightly etching an end face of the porous layer to facilitate the subsequent separation of the semiconductor layer from the substrate.

104. A method according to Claim 97, wherein said at least one semiconductor layer is formed by epitaxial growth using Chemical Vapor Deposition.

#### REMARKS

Claims 97-104 are now pending. Previously pending claims 22-96, which had been added in the Preliminary Amendment filed September 29, 1999, have been canceled without prejudice or disclaimer of subject matter. Claims 97 and 102 are the independent claims. Claims 97-102 have been copied from U.S. Patent No. 5,811,348, copy attached at TAB A, which issued September 22, 1998.

Applicants wish to personally interview the Examiner in this case before any action on the merits. Accordingly, before taking up this application, the Examiner is kindly requested to contact the undersigned attorney to

arrange an interview in the event the interview has not yet taken place.

Applicants' undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should continue to be directed to our below listed address.

Respectfully submitted,

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